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Logic level TOPFET

BUK118-50DL

DESCRIPTION

Monolithic temperature and overload protected logic level power MOSFET in **TOPFET2** technology assembled in a 3 pin plastic package.

APPLICATIONS

General purpose switch for driving

- lamps
- motors
- solenoids
- heaters

in automotive systems and other applications.

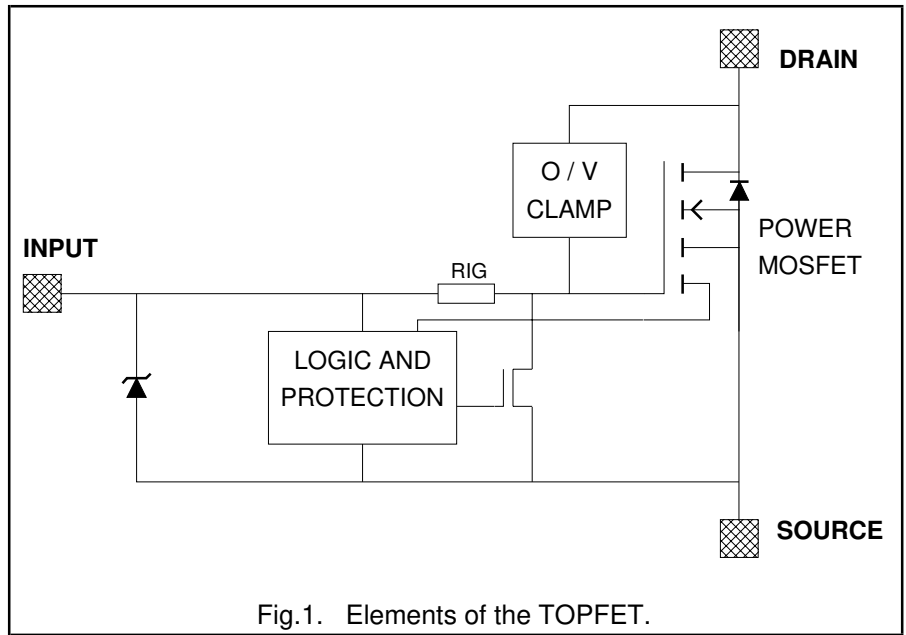
FEATURES

- TrenchMOS output stage
- Current limiting
- Overload protection
- Overtemperature protection
- Protection latched reset by input
- 5 V logic compatible input level
- Control of output stage and supply of overload protection circuits derived from input
- Low operating input current permits direct drive by micro-controller
- ESD protection on all pins
- Overvoltage clamping for turn off of inductive loads

QUICK REFERENCE DATA

| SYMBOL | PARAMETER | MAX. | UNIT |
|--------------|--|------|------|
| V_{DS} | Continuous drain source voltage | 50 | V |
| I_D | Continuous drain current | 16 | A |
| P_D | Total power dissipation | 65 | W |
| T_j | Continuous junction temperature | 150 | °C |
| $R_{DS(ON)}$ | Drain-source on-state resistance | 50 | mΩ |
| I_{ISL} | Input supply current $V_{IS} = 5\text{ V}$ | 650 | μA |

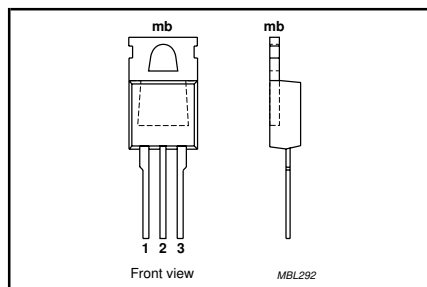
FUNCTIONAL BLOCK DIAGRAM



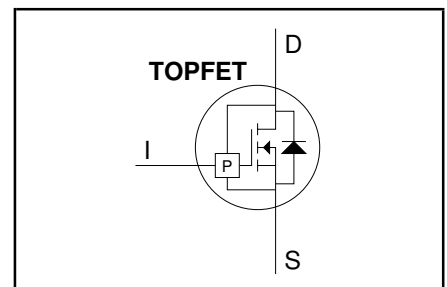
PINNING - SOT78B

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | input |
| 2 | drain |
| 3 | source |
| tab | drain |

PIN CONFIGURATION



SYMBOL



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LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------|--|--|------|----------------|------------------|
| V_{DS} | Continuous drain source voltage ¹ | - | - | 50 | V |
| I_D | Continuous drain current | $V_{IS} = 5 \text{ V}; T_{mb} = 25 \text{ }^\circ\text{C}$ | - | self - limited | A |
| I_D | Continuous drain current | $V_{IS} = 5 \text{ V}; T_{mb} \leq 125 \text{ }^\circ\text{C}$ | - | 16 | A |
| I_I | Continuous input current | - | -5 | 5 | mA |
| I_{IRM} | Non-repetitive peak input current | $t_p \leq 1 \text{ ms}$ | -10 | 10 | mA |
| P_D | Total power dissipation | $T_{mb} \leq 25 \text{ }^\circ\text{C}$ | - | 65 | W |
| T_{stg} | Storage temperature | - | -55 | 175 | $^\circ\text{C}$ |
| T_j | Continuous junction temperature ² | normal operation | - | 150 | $^\circ\text{C}$ |
| T_{sold} | Lead temperature | during soldering | - | 260 | $^\circ\text{C}$ |

ESD LIMITING VALUE

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|--------|---|--|------|------|------|
| V_C | Electrostatic discharge capacitor voltage | Human body model; $C = 250 \text{ pF}; R = 1.5 \text{ k}\Omega$ | - | 2 | kV |

OVERVOLTAGE CLAMPING LIMITING VALUES

At a drain source voltage above 50 V the power MOSFET is actively turned on to clamp overvoltage transients.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|--|--|------|------|------|
| E_{DSM} | Inductive load turn-off Non-repetitive clamping energy | $I_{DM} = 16 \text{ A}; V_{DD} \leq 20 \text{ V}$ $T_{mb} \leq 25 \text{ }^\circ\text{C}$ | - | 200 | mJ |
| E_{DRM} | Repetitive clamping energy | $T_{mb} \leq 95 \text{ }^\circ\text{C}; f = 250 \text{ Hz}$ | - | 32 | mJ |

OVERLOAD PROTECTION LIMITING VALUE

With an adequate protection supply provided via the input pin, TOPFET can protect itself from two types of overload - overtemperature and short circuit load.

| SYMBOL | PARAMETER | REQUIRED CONDITION | MIN. | MAX. | UNIT |
|----------|-----------------------------------|--|------|------|------|
| V_{DS} | Drain source voltage ³ | $4 \text{ V} \leq V_{IS} \leq 5.5 \text{ V}$ | 0 | 35 | V |

THERMAL CHARACTERISTIC

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|----------------|--|------------|------|------|------|------|
| $R_{th\ j-mb}$ | Thermal resistance Junction to mounting base | - | - | 1.75 | 1.92 | K/W |

¹ Prior to the onset of overvoltage clamping. For voltages above this value, safe operation is limited by the overvoltage clamping energy.² A higher T_j is allowed as an overload condition but at the threshold $T_{j(TO)}$ the over temperature trip operates to protect the switch.³ All control logic and protection functions are disabled during conduction of the source drain diode.

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OUTPUT CHARACTERISTICSLimits are for $-40^{\circ}\text{C} \leq T_{\text{mb}} \leq 150^{\circ}\text{C}$; typicals are for $T_{\text{mb}} = 25^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-----------------------------|---|--|------|------|------|------------------|
| $V_{(\text{CL})\text{DSS}}$ | Off-state Drain-source clamping voltage | $V_{\text{IS}} = 0 \text{ V}$ | 50 | - | - | V |
| | | $I_{\text{D}} = 10 \text{ mA}$ $I_{\text{DM}} = 2 \text{ A}; t_{\text{p}} \leq 300 \mu\text{s}; \delta \leq 0.01$ | 50 | 60 | 70 | V |
| I_{DSS} | Drain source leakage current | $V_{\text{DS}} = 40 \text{ V}$ | - | - | 100 | μA |
| | | $T_{\text{mb}} = 25^{\circ}\text{C}$ | - | 0.1 | 10 | μA |
| $R_{\text{DS(ON)}}$ | On-state Drain-source resistance | $I_{\text{DM}} = 6 \text{ A}; t_{\text{p}} \leq 300 \mu\text{s}; \delta \leq 0.01$ | - | - | 95 | $\text{m}\Omega$ |
| | | $V_{\text{IS}} \geq 4.4 \text{ V}$ | - | 36 | 50 | $\text{m}\Omega$ |
| | | $T_{\text{mb}} = 25^{\circ}\text{C}$ | - | - | 100 | $\text{m}\Omega$ |
| | | $V_{\text{IS}} \geq 4 \text{ V}$ | - | 39 | 55 | $\text{m}\Omega$ |

OVERLOAD CHARACTERISTICS $-40^{\circ}\text{C} \leq T_{\text{mb}} \leq 150^{\circ}\text{C}$ unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--|--|--|------|------|------|--------------------|
| I_{D} | Short circuit load Drain current limiting | $V_{\text{DS}} = 13 \text{ V}$ | 16 | 24 | 32 | A |
| | | $V_{\text{IS}} = 5 \text{ V};$ $4.4 \text{ V} \leq V_{\text{IS}} \leq 5.5 \text{ V}$ | 12 | - | 36 | A |
| | | $4 \text{ V} \leq V_{\text{IS}} \leq 5.5 \text{ V}$ | 8 | - | 36 | A |
| $P_{\text{D(TO)}}$ T_{DSC} | Overload protection Overload power threshold Characteristic time | $V_{\text{IS}} = 5 \text{ V}; T_{\text{mb}} = 25^{\circ}\text{C}$ | 40 | 120 | 160 | W |
| | | device trips if $P_{\text{D}} > P_{\text{D(TO)}}$ which determines trip time ¹ | 200 | 350 | 600 | μs |
| $T_{\text{j(TO)}}$ | Overtemperature protection Threshold junction temperature ² | | 150 | 170 | - | $^{\circ}\text{C}$ |

¹ Trip time $t_{\text{d,sc}}$ varies with overload dissipation P_{D} according to the formula $t_{\text{d,sc}} \approx T_{\text{DSC}} / \ln[P_{\text{D}} / P_{\text{D(TO)}}]$.² This is independent of the dV/dt of input voltage V_{IS} .

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INPUT CHARACTERISTICS

The supply for the logic and overload protection is taken from the input.

Limits are for $-40^{\circ}\text{C} \leq T_{\text{mb}} \leq 150^{\circ}\text{C}$; typicals are for $T_{\text{mb}} = 25^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|---------------------|---|--|------|------|------|------------------|
| $V_{\text{IS(TO)}}$ | Input threshold voltage | $V_{\text{DS}} = 5 \text{ V}; I_{\text{D}} = 1 \text{ mA}$ $T_{\text{mb}} = 25^{\circ}\text{C}$ | 0.6 | - | 2.4 | V |
| | | | 1.1 | 1.6 | 2.1 | V |
| I_{IS} | Input supply current | normal operation; $V_{\text{IS}} = 5 \text{ V}$ $V_{\text{IS}} = 4 \text{ V}$ | 100 | 220 | 400 | μA |
| | | | 80 | 195 | 330 | μA |
| I_{ISL} | Input supply current | protection latched; $V_{\text{IS}} = 5 \text{ V}$ $V_{\text{IS}} = 3 \text{ V}$ | 200 | 400 | 650 | μA |
| | | | 130 | 250 | 430 | μA |
| V_{ISR} | Protection reset voltage ¹ | reset time $t_{\text{r}} \geq 100 \mu\text{s}$ | 1.5 | 2 | 2.9 | V |
| t_{r} | Latch reset time | $V_{\text{IS1}} = 5 \text{ V}, V_{\text{IS2}} < 1 \text{ V}$ | 10 | 40 | 100 | μs |
| $V_{\text{(CL)IS}}$ | Input clamping voltage | $I_{\text{I}} = 1.5 \text{ mA}$ | 5.5 | - | 8.5 | V |
| R_{IG} | Input series resistance ² to gate of power MOSFET | $T_{\text{mb}} = 25^{\circ}\text{C}$ | - | 33 | - | $\text{k}\Omega$ |

SWITCHING CHARACTERISTICS

$T_{\text{mb}} = 25^{\circ}\text{C}$; $V_{\text{DD}} = 13 \text{ V}$; resistive load $R_{\text{L}} = 4 \Omega$. Refer to waveform figure and test circuit.

| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--------------------|---------------------|-------------------------------|------|------|------|---------------|
| $t_{\text{d on}}$ | Turn-on delay time | $V_{\text{IS}} = 5 \text{ V}$ | - | 15 | 30 | μs |
| t_{r} | Rise time | | - | 30 | 60 | μs |
| $t_{\text{d off}}$ | Turn-off delay time | $V_{\text{IS}} = 0 \text{ V}$ | - | 70 | 140 | μs |
| t_{f} | Fall time | | - | 35 | 70 | μs |

¹ The input voltage below which the overload protection circuits will be reset.

² Not directly measurable from device terminals.

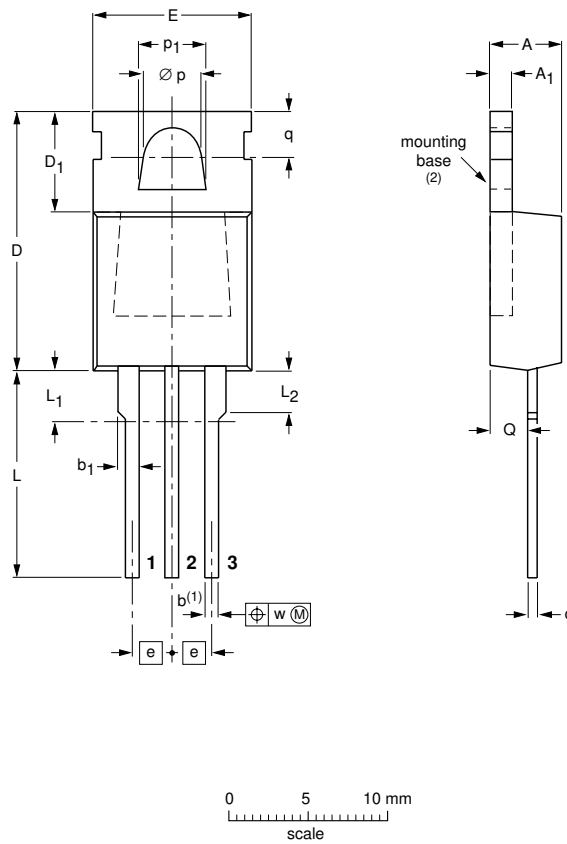
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MECHANICAL DATA

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-leads

SOT78B



DIMENSIONS (mm are the original dimensions)

| UNIT | A | A ₁ | b ⁽¹⁾ | b ₁ | c | D | D ₁ | E | e | L | L ₁ | L ₂ max. | ∅ p | p ₁ | q | Q | w |
|------|------------|----------------|------------------|----------------|------------|--------------|----------------|-------------|------|--------------|----------------|---------------------|------------|----------------|------------|------------|-----|
| mm | 4.5 4.1 | 1.39 1.27 | 0.85 0.60 | 1.3 1.0 | 0.7 0.4 | 15.8 15.2 | 6.4 5.9 | 10.3 9.7 | 2.54 | 15.0 13.5 | 3.30 2.79 | 3.0 | 3.8 3.6 | 4.3 4.1 | 3.0 2.7 | 2.6 2.2 | 0.4 |

Notes

1. The positional accuracy of the terminals is controlled within zone L₁ max.
2. Mounting base configuration is not defined within the dimensions E and D

| OUTLINE VERSION | REFERENCES | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|-------|------|---------------------|------------|
| | IEC | JEDEC | EIAJ | | |
| SOT78B | | | | | 01-02-22 |

Fig.2. SOT78B (TO220AB) package¹, pin 2 connected to mounting base.

¹ Refer to mounting instructions for SOT78 (TO220) envelopes. Epoxy meets UL94 V0 at 1/8". Net mass: 2 g

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DEFINITIONS

| DATA SHEET STATUS | | |
|--|-----------------------------------|---|
| DATA SHEET STATUS¹ | PRODUCT STATUS² | DEFINITIONS |
| Objective data | Development | This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice |
| Preliminary data | Qualification | This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product |
| Product data | Production | This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A |
| Limiting values | | |
| Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability. | | |
| Application information | | |
| Where application information is given, it is advisory and does not form part of the specification. | | |
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¹ Please consult the most recently issued datasheet before initiating or completing a design.

² The product status of the device(s) described in this datasheet may have changed since this datasheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.